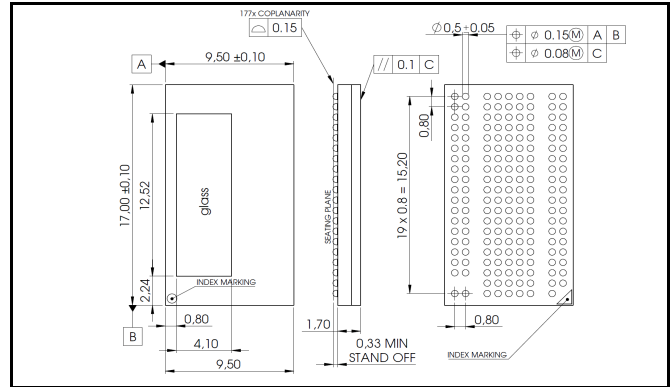
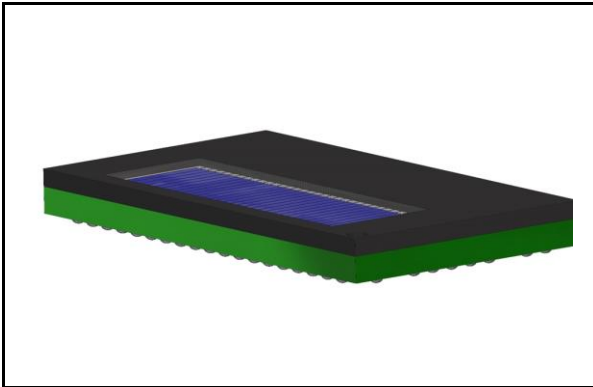


Engineering Samples



Features

- 32 element APD array
- High QE >80% for $\lambda = 760-910$ nm
- High speed, low noise

Description

Matrix APD array for NIR detection. PCB based BGA package. AR coated glass glued on active area of the APD. Non hermetic, suitable for reflow soldering.

Application

Automotive and industrial LiDAR (AECQ-102 pending)

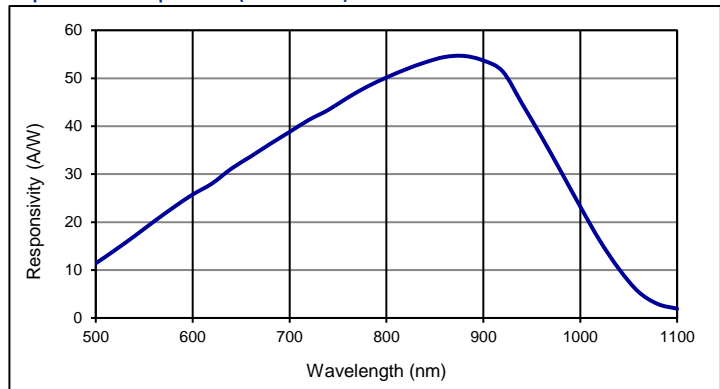
RoHS

2011/65/EU

Absolute maximum ratings

Symbol	Parameter	Min	Max	Unit
T_{STG}	Storage temp	-40	125	°C
T_{OP}	Operating temp	-40	125	°C
M_{max}	Gain ($I_{PO} = 1$ nA)	200		
I_{PEAK}	Peak DC current (linearity)		0.25	mA

Spectral response (M = 100)



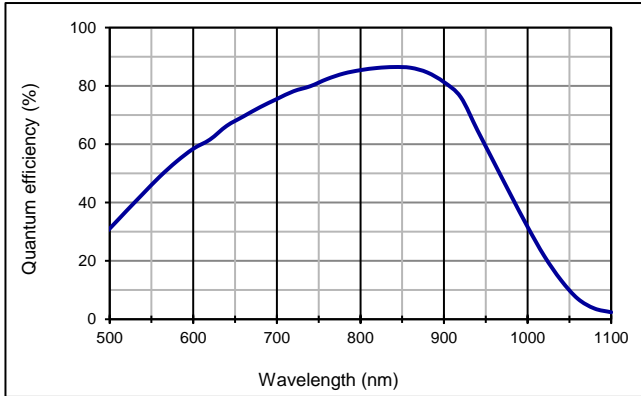
Electro-optical characteristics @ 23°C

Symbol	Characteristic	Test Condition	Min	Typ	Max	125°C*	Unit
	No of elements		32				
	Active area		340 x 3600				μm
	Gap; Pitch		40 ; 380				μm
I_D	Dark current	M = 50, per element		0.25	1.5	1500	nA
C	Capacitance	M = 50, per element			3		pF
	Responsivity	M = 100; $\lambda = 905$ nm	49.5	55			A/W
t_R	Rise time	M = 100; $\lambda = 905$ nm; $R_L = 50 \Omega$			1.5		ns
V_{BR}	Breakdown voltage	$I_R = 10 \mu A$	160		240	400	V
	Temperature coefficient	Ubr		1.49			V/K
	Cross talk suppression**	DC, M=50, $\lambda = 905$ nm	50				dB
	Gain uniformity	M = 50		± 10	± 30		%
	Excess Noise factor	M=100		2.5			
t	Cover glass thickness			300			μm
Tabs	ARC on cover glass	880 nm to 940 nm; AOI $_{max}$ =45°	98	99			%

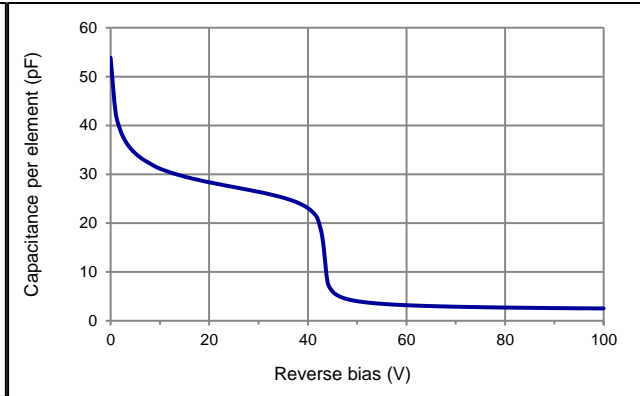
* maximal value

** middle of pixel, spot size = 10 μm diameter, optical power = 1 μW/mm²

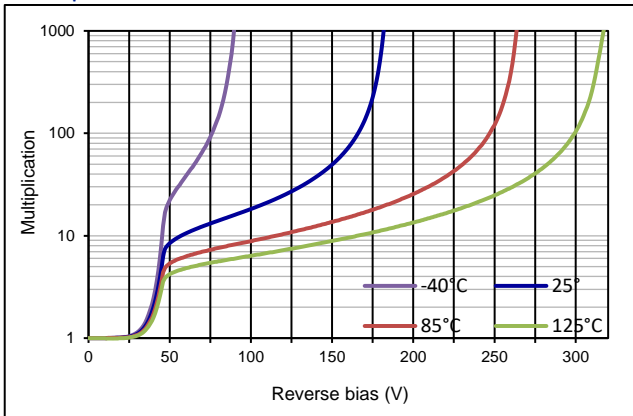
Quantum efficiency (23 °C)



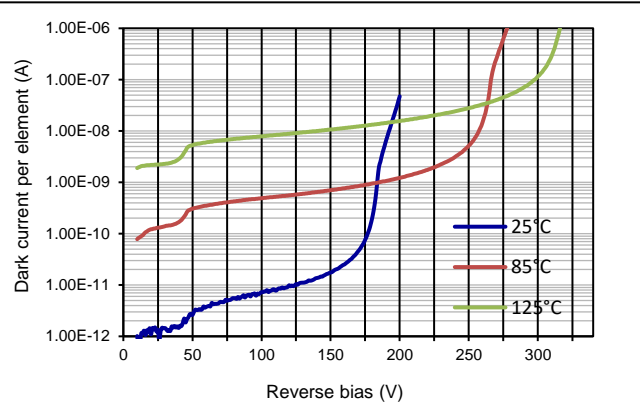
Capacitance as fct of reverse bias (23 °C)



Multiplication as fct of reverse bias***

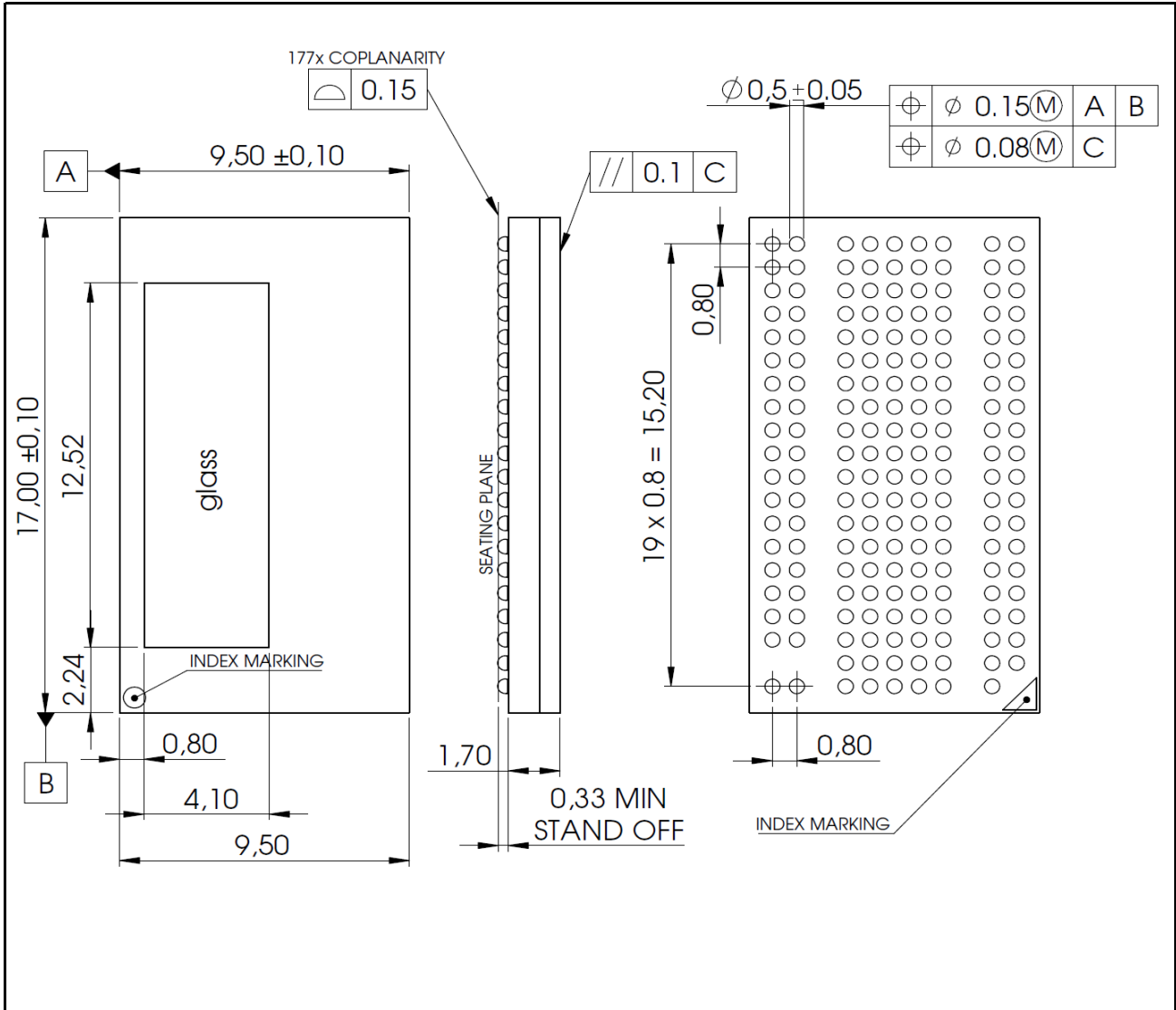


Dark current as fct of reverse bias



*** Illumination with 10 nW optical power

Technical Drawing, Package BGA



Pinning (bottom view)

	11	10	9	8	7	6	5	4	3	2	1
T	n.c.	n.c.		n.c.	n.c.	n.c.	n.c.	n.c.		n.c.	n.c.
S	Gnd	G		n.c.	n.c.	n.c.	n.c.	n.c.		n.c.	n.c.
R	C32	C31		n.c.	n.c.	n.c.	n.c.	n.c.		n.c.	n.c.
Q	C30	C29		n.c.	n.c.	n.c.	n.c.	n.c.		n.c.	n.c.
P	C28	C27		n.c.	n.c.	n.c.	n.c.	n.c.		n.c.	n.c.
O	C26	C25		n.c.	n.c.	n.c.	n.c.	n.c.		n.c.	n.c.
N	C24	C23		n.c.	n.c.	n.c.	n.c.	n.c.		n.c.	n.c.
M	C22	C21		n.c.	n.c.	n.c.	n.c.	n.c.		n.c.	n.c.
L	C20	C19		n.c.	n.c.	n.c.	n.c.	n.c.		n.c.	n.c.
K	C18	C17		n.c.	n.c.	n.c.	n.c.	n.c.		n.c.	n.c.
J	C16	C15		n.c.	n.c.	n.c.	n.c.	n.c.		n.c.	n.c.
I	C14	C13		n.c.	n.c.	n.c.	n.c.	n.c.		n.c.	n.c.
H	C12	C11		n.c.	n.c.	n.c.	n.c.	n.c.		n.c.	n.c.
G	C10	C9		n.c.	n.c.	n.c.	n.c.	n.c.		n.c.	n.c.
F	C8	C7		n.c.	n.c.	n.c.	n.c.	n.c.		n.c.	n.c.
E	C6	C5		n.c.	n.c.	n.c.	n.c.	n.c.		n.c.	n.c.
D	C4	C3		n.c.	n.c.	n.c.	n.c.	n.c.		n.c.	n.c.
C	C2	C1		n.c.	n.c.	n.c.	n.c.	n.c.		n.c.	n.c.
B				n.c.	n.c.	n.c.	n.c.	n.c.		n.c.	n.c.
A	A	A		n.c.	n.c.	n.c.	n.c.	n.c.		n.c.	

- A Anode
- C Cathode
- N.C. not connected
- G Guard
- Gnd Ground

Package dimension

For small quantities chip trays are available.

Handling:

Please refer to document "Instructions for handling and processing"

Application hints:

Please refer to document: "application-note-apd-array"